## EE 362 Electronic, Magnetic, & Opt. Prop. of Mat'ls Quiz 4 (Spring 2025)

Name <u>KEY A</u>

Instructions: Open book/notes. Place answers in indicated spaces and show all work for credit. Carry *at least* **6** significant figures on constants/parameters in calculations. Give answers with **4-5** significant figures.

A sample of gallium arsenide (GaAs) has an intrinsic carrier concentration of  $1.79 \times 10^6$  #/cm<sup>3</sup> and a band gap of 1.424 eV at 300 K. It is doped with tellurium at a concentration of  $2 \times 10^{14}$  #/cm<sup>3</sup>. Is the sample a p-type or n-type extrinsic semiconductor? Find the conduction band electron concentration  $n_0$  (#/cm<sup>3</sup>) and valence hole concentration  $p_0$  (#/cm<sup>3</sup>). Calculate the **magnitude** of the difference between the intrinsic Fermi energy and the Fermi energy of the sample in eV, i.e.,  $\Delta E = |E_F - E_{Fi}|$ . Is  $E_F$  bigger or smaller than  $E_{Fi}$ ?

Tellurium (Te) is a column to the right of arsenic (As) on periodic table  $\Rightarrow$  donor  $\Rightarrow$  <u>**n-type**</u>

Given that  $N_d = 2 \times 10^{14} \, \text{#/cm}^3 >> n_i = 1.79 \times 10^6 \, \text{#/cm}^3$  and  $N_a = 0$ ,  $\underline{n_0} \cong N_d = 2 \times 10^{14} \, \text{#/cm}^3$ . Or, can use (4.60),

$$n_{0} = \frac{N_{d} - N_{a}}{2} + \sqrt{\left(\frac{N_{d} - N_{a}}{2}\right)^{2} + n_{i}^{2}} = \frac{2 \times 10^{14} - 0}{2} + \sqrt{\left(\frac{2 \times 10^{14} - 0}{2}\right)^{2} + \left(1.79 \times 10^{6}\right)^{2}} \text{ to get}$$
$$\Rightarrow \underline{n_{0}} \cong N_{d} = 2 \times 10^{14} \text{ #/cm}^{3}.$$

Per (4.43),  $n_i^2 = n_0 p_0 \implies p_0 = n_i^2 / n_0 = (1.79 \times 10^6)^2 / 2 \times 10^{14} \implies \underline{p_0 = 0.0160205 \ \#/\text{cm}^3}$ .

Per (4.65), 
$$E_F - E_{Fi} = k_B T \ln\left(\frac{n_0}{n_i}\right) = 8.617333 \times 10^{-5} (300) \ln\left(\frac{2 \times 10^{14}}{1.79 \times 10^6}\right)$$
  
 $\Rightarrow \Delta E = |E_F - E_{Fi}| = 0.47908 \text{ eV}.$ 

p-type or **n-type**? (circle correct)  $n_0 = \underline{N_d} = 2 \times 10^{14} \, \text{#/cm}^3$   $p_0 = \underline{0.0160205 \, \text{#/cm}^3}$  $\Delta E = \underline{0.47908 \, \text{eV}} \qquad E_F > E_{Fi} \text{ or } E_{Fi} > E_F? \text{ (circle correct)}$ 

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## EE 362 Electronic, Magnetic, & Opt. Prop. of Mat'ls Quiz 4 (Spring 2025)

Name <u>KEY B</u>

Instructions: Open book/notes. Place answers in indicated spaces and show all work for credit. Carry *at least* **6** significant figures on constants/parameters in calculations. Give answers with **4-5** significant figures.

A sample of gallium arsenide (GaAs) has an intrinsic carrier concentration of  $1.79 \times 10^6 \text{ #/cm}^3$  and a band gap of 1.424 eV at 300 K. It is doped with cadmium at a concentration of  $6 \times 10^{14} \text{ #/cm}^3$ . Is the sample a p-type or n-type extrinsic semiconductor? Find the conduction band electron concentration  $n_0$  (#/cm<sup>3</sup>) and valence hole concentration  $p_0$  (#/cm<sup>3</sup>). Calculate the **magnitude** of the difference between the intrinsic Fermi energy and the Fermi energy of the sample in eV, i.e.,  $\Delta E = |E_F - E_{Fi}|$ . Is  $E_F$  bigger or smaller than  $E_{Fi}$ ?

Cadmium (Cd) is a column to the left of Gallium (Ga) on periodic table  $\Rightarrow$  acceptor  $\Rightarrow$  <u>**p-type**</u>

Given that  $N_a = 6 \times 10^{14} \, \text{#/cm}^3 >> n_i = 1.79 \times 10^6 \, \text{#/cm}^3$  and  $N_d = 0$ ,  $\underline{p_0} \cong N_a = 6 \times 10^{14} \, \text{#/cm}^3$ . Or, can use (4.62),

$$p_{0} = \frac{N_{a} - N_{d}}{2} + \sqrt{\left(\frac{N_{a} - N_{d}}{2}\right)^{2} + n_{i}^{2}} = \frac{6 \times 10^{14} - 0}{2} + \sqrt{\left(\frac{6 \times 10^{14} - 0}{2}\right)^{2} + \left(1.79 \times 10^{6}\right)^{2}} \text{ to get}$$
$$\Rightarrow \underline{p_{0}} \cong N_{a} = 6 \times 10^{14} \text{ #/cm}^{3}.$$

Per (4.43),  $n_i^2 = n_0 p_0 \implies n_0 = n_i^2 / p_0 = (1.79 \times 10^6)^2 / 6 \times 10^{14} \implies \underline{n_0} = 0.0053402 \ \text{\#/cm}^3$ .

Per (4.68), 
$$E_{Fi} - E_F = k_B T \ln\left(\frac{p_0}{n_i}\right) = 8.617333 \times 10^{-5} (300) \ln\left(\frac{6 \times 10^{14}}{1.79 \times 10^6}\right) = 0.50748055$$
  

$$\Rightarrow \Delta E = |E_F - E_{Fi}| = 0.50748 \text{ eV}.$$

p-type	or n-type ? (circle correct)	$n_0 = 0.0053402 \ \text{\#/cm}^3$	$p_0 = \mathbf{\underline{6} \times 10^{14} \ \#/cm^3}$	
	$\Delta E = \mathbf{\underline{0.50748 eV}}$	$E_F > E_{Fi}$ or $E_{Fi} >$	$E_F$ ? (circle correct)	

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